FAIRCHILD

40V N-Channel PowerTrench[®] MOSFET

General Description

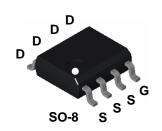
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

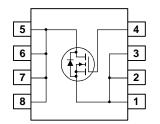
Applications

• DC/DC converter

Features

- 11 A, 40 V. $R_{DS(ON)} = 13 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- High performance trench technology for extremely low $R_{\text{DS}(\text{ON})}$
- Low gate charge (35 nC typical)
- High power and current handling capability





Absolute Maximum Ratings T_{A=25°C} unless otherwise noted

Symbol	Parameter		Ratings	Units	
V _{DSS}	Drain-Source Voltage		40	V	
V _{GSS}	Gate-Source Voltage		±12	V	
ID	Drain Current – Continuous	(Note 1a)	11	A	
	– Pulsed		50		
PD	Power Dissipation for Single Operation	(Note 1a)	2.5	W	
		(Note 1b)	1.4		
		(Note 1c)	1.2		
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to +175	°C	

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity	
FDS4672A	FDS4672A	13"	12mm	2500 units	

Electrical Characteristics T _A = 25°C unless otherwise noted						
Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	40			V
<u>ΔBVdss</u> ΔTj	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$, Referenced to 25°C		37		mV/°
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 12 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -12 V V_{DS} = 0 V$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	0.8	1.2	2.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$, Referenced to 25°C		-4		mV/°
R _{DS(on)}	Static Drain–Source On–Resistance	V _{GS} = 4.5 V, I _D = 11 A V _{GS} =4.5 V, I _D =11A, T _J =125°C		10 15	13 21	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	50			Α
g _{FS}	Forward Transconductance	$V_{DS} = 5 V, I_{D} = 11 A$		65		S
Dvnamio	Characteristics					
Ciss	Input Capacitance	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$		4766		pF
Coss	Output Capacitance	f = 1.0 MHz		346		pF
Crss	Reverse Transfer Capacitance			155		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn–On Delay Time	$V_{DD} = 20 V$, $I_D = 1 A$,		17	31	ns
t _r	Turn–On Rise Time	$V_{GS} = 4.5 V, R_{GEN} = 6 \Omega$		9	18	ns
t _{d(off)}	Turn–Off Delay Time			43	68	ns
t _f	Turn–Off Fall Time	_		14	25	ns
Q _q	Total Gate Charge	$V_{DS} = 20 V, I_D = 11 A,$		35	49	nC
Q _{qs}	Gate–Source Charge	$V_{GS} = 4.5 V$		7.8		nC
Q _{gd}	Gate–Drain Charge			8.8		nC
-	ource Diode Characteristics	and Maximum Ratings				1
	Maximum Continuous Drain–Source				2.1	Α
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 V$, $I_S = 2.1 A$ (Note 2)		0.7	1.2	V

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50°/W when mounted on a 1in² pad of 2 oz copper

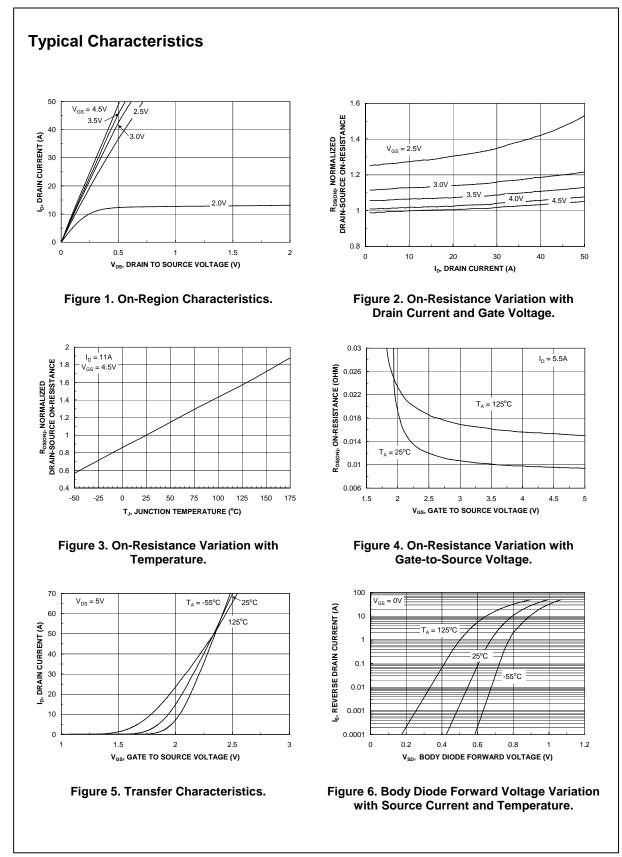
b) 105°/W when mounted on a .04 in² pad of 2 oz copper

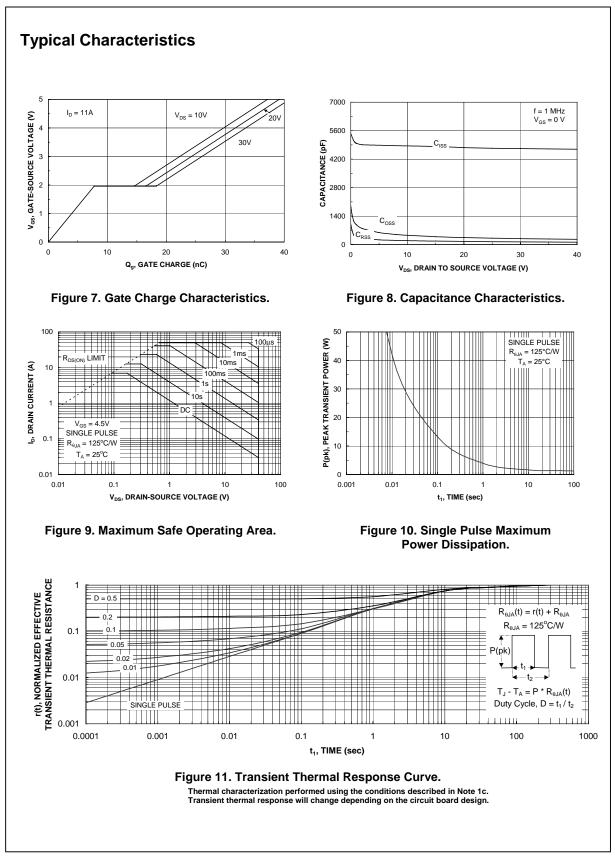
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c) 125°/W when mounted on a minimum pad.

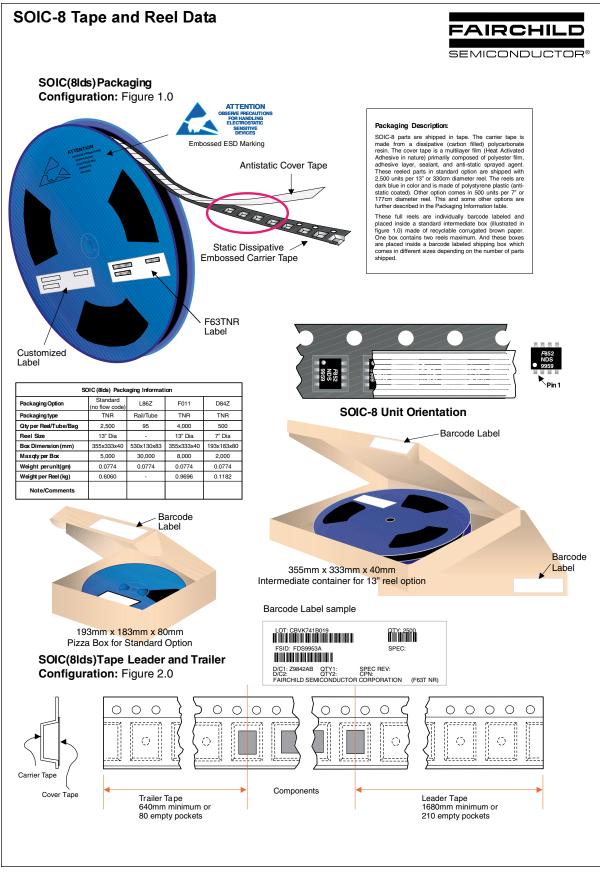
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%



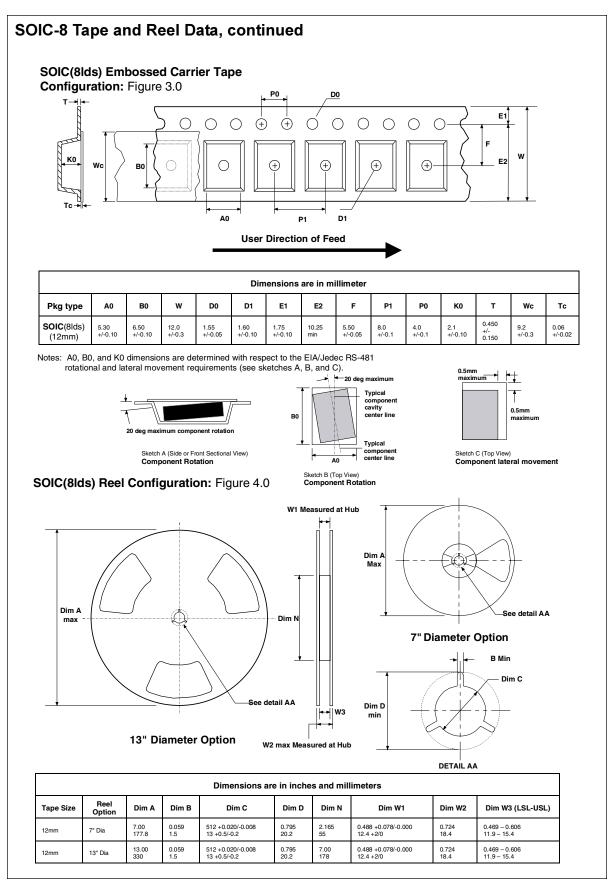


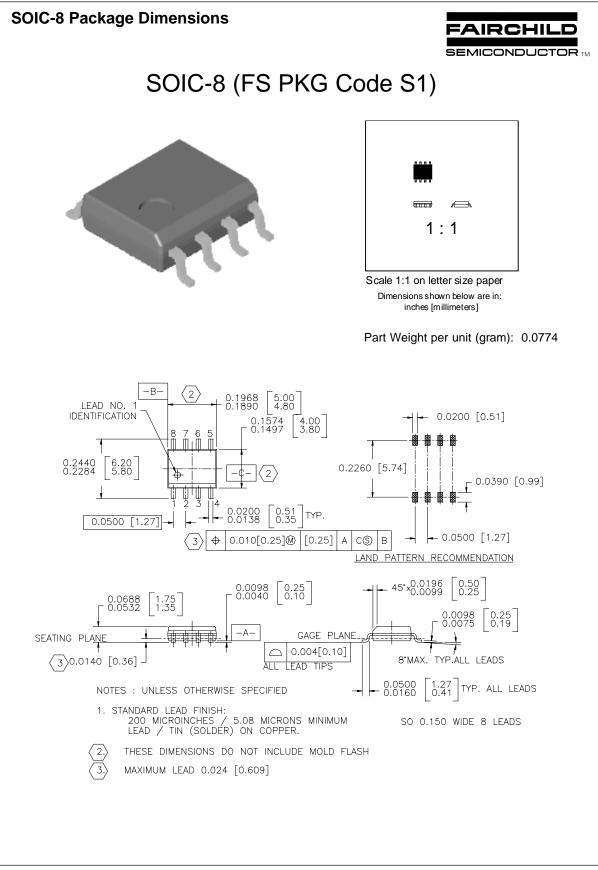
FDS4672A Rev C(W)



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